

FEATURES

- 10µs Short Circuit Withstand
- High Thermal Cycling Capability
- Non Punch Through Silicon
- Isolated AISiC Base with AlN Substrates
- Lead Free construction

APPLICATIONS

- High Reliability Inverters
- Motor Controllers
- Traction Drives

The Powerline range of high power modules includes half bridge, chopper, dual, single and bi-directional switch configurations covering voltages from 600V to 3300V and currents up to 2400A.

The DIM800DCM12-A000 is a 1200V, n-channel enhancement mode, insulated gate bipolar transistor (IGBT) chopper module. The IGBT has a wide reverse bias safe operating area (RBSOA) plus 10µs short circuit withstand. This device is optimised for traction drives and other applications requiring high thermal cycling capability.

The module incorporates an electrically isolated base plate and low inductance construction enabling circuit designers to optimise circuit layouts and utilise grounded heat sinks for safety.

ORDERING INFORMATION

Order As:

DIM800DCM12-A000

Note: When ordering, please use the complete part number

KEY PARAMETERS

V_{CES}	1200V
$V_{CE(sat)}$ * (typ)	2.7V
I_C (max)	800A
$I_{C(PK)}$ (max)	1600A

* Measured at the power busbars, not the auxiliary terminals

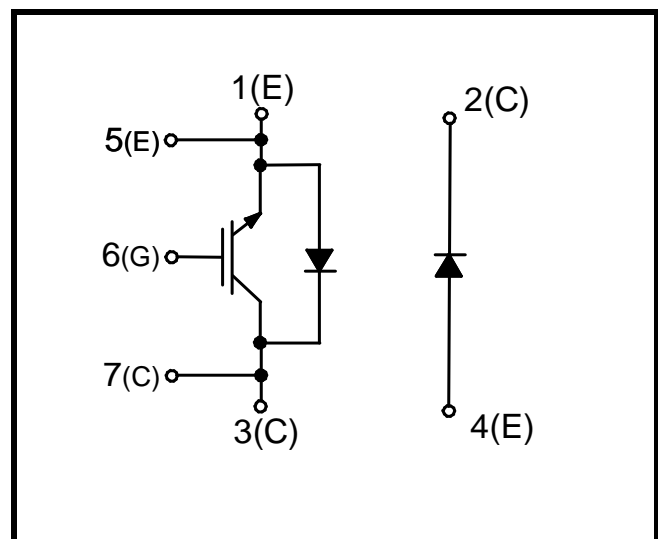


Fig. 1 Circuit configuration

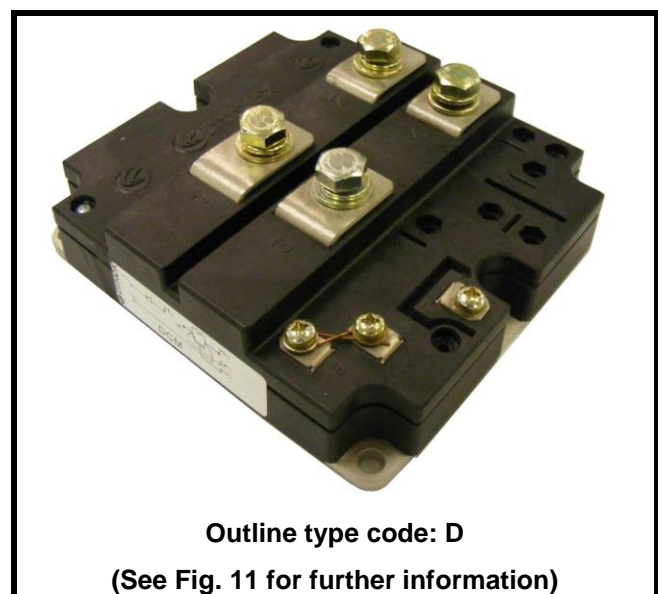


Fig. 2 Package

ABSOLUTE MAXIMUM RATINGS

Stresses above those listed under 'Absolute Maximum Ratings' may cause permanent damage to the device. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture of the package. Appropriate safety precautions should always be followed. Exposure to Absolute Maximum Ratings may affect device reliability.

$T_{case} = 25^{\circ}\text{C}$ unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
V_{CES}	Collector-emitter voltage	$V_{GE} = 0\text{V}$	1200	V
V_{GES}	Gate-emitter voltage		± 20	V
I_C	Continuous collector current	$T_{case} = 85^{\circ}\text{C}$	800	A
$I_{C(PK)}$	Peak collector current	1ms, $T_{case} = 115^{\circ}\text{C}$	1600	A
P_{max}	Max. transistor power dissipation	$T_{case} = 25^{\circ}\text{C}$, $T_j = 150^{\circ}\text{C}$	6940	W
I^2t	Diode I^2t value (IGBT arm)	$V_R = 0$, $t_p = 10\text{ms}$, $T_j = 125^{\circ}\text{C}$	100	kA^2s
	Diode I^2t value (Diode arm)		225	kA^2s
V_{isol}	Isolation voltage – per module	Commoned terminals to base plate. AC RMS, 1 min, 50Hz	2500	V
Q_{PD}	Partial discharge – per module	IEC1287, $V_1 = 1800\text{V}$, $V_2 = 1300\text{V}$, 50Hz RMS	10	pC

THERMAL AND MECHANICAL RATINGS

Internal insulation material:	AlN
Baseplate material:	AlSiC
Creepage distance:	20mm
Clearance:	10mm
CTI (Comparative Tracking Index):	<600

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
$R_{th(j-c)}$	Thermal resistance – transistor (per arm)	Continuous dissipation – junction to case	-	-	18	$^{\circ}\text{C}/\text{kW}$
$R_{th(j-c)}$	Thermal resistance – diode (IGBT arm)	Continuous dissipation – junction to case	-	-	40	$^{\circ}\text{C}/\text{kW}$
	Thermal resistance – diode (Diode arm)		-	-	26.7	$^{\circ}\text{C}/\text{kW}$
$R_{th(c-h)}$	Thermal resistance – case to heatsink (per module)	Mounting torque 5Nm (with mounting grease)	-	-	8	$^{\circ}\text{C}/\text{kW}$
T_j	Junction temperature	Transistor	-	-	150	$^{\circ}\text{C}$
		Diode	-	-	125	$^{\circ}\text{C}$
T_{stg}	Storage temperature range	-	-40	-	125	$^{\circ}\text{C}$
	Screw torque	Mounting – M6	-	-	5	Nm
		Electrical connections – M4	-	-	2	Nm
		Electrical connections – M8	-	-	10	Nm

ELECTRICAL CHARACTERISTICS
T_{case} = 25°C unless stated otherwise.

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
I _{CES}	Collector cut-off current	V _{GE} = 0V, V _{CE} = V _{CES}			1	mA
		V _{GE} = 0V, V _{CE} = V _{CES} , T _{case} = 125°C			25	mA
I _{GES}	Gate leakage current	V _{GE} = ± 20V, V _{CE} = 0V			4	μA
V _{GE(TH)}	Gate threshold voltage	I _C = 20mA, V _{GE} = V _{CE}	4.5	5.5	6.5	V
V _{CE(sat)}	Collector-emitter saturation voltage	V _{GE} = 15V, I _C = 800A		2.2	2.8	V
		V _{GE} = 15V, I _C = 800A, T _j = 125°C		2.6	3.2	V
I _F	Diode forward current	DC			800	A
I _{FM}	Diode maximum forward current	t _p = 1ms			1600	A
V _F	Diode forward voltage (IGBT arm)	I _F = 800A		2.1	2.4	V
	Diode forward voltage (Diode arm)			1.8	2.1	V
	Diode forward voltage (IGBT arm)	I _F = 800A, T _j = 125°C		2.1	2.4	V
	Diode forward voltage (Diode arm)			1.7	2.0	V
C _{ies}	Input capacitance	V _{CE} = 25V, V _{GE} = 0V, f = 1MHz		90		nF
Q _g	Gate charge	±15V		9		μC
C _{res}	Reverse transfer capacitance	V _{CE} = 25V, V _{GE} = 0V, f = 1MHz				nF
L _M	Module inductance – per arm			20		nH
R _{INT}	Internal transistor resistance – per arm			270		μΩ
SC _{Data}	Short circuit current, I _{SC}	T _j = 125°C, V _{CC} = 900V t _p ≤ 10μs, V _{GE} ≤ 15V V _{CE(max)} = V _{CES} - L* x di/dt IEC 60747-9		4500		A

Note:

 * L is the circuit inductance + L_M

ELECTRICAL CHARACTERISTICS

$T_{case} = 25^{\circ}\text{C}$ unless stated otherwise

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units	
$t_{d(off)}$	Turn-off delay time	$I_C = 800\text{A}$ $V_{GE} = \pm 15\text{V}$ $V_{CE} = 600\text{V}$ $R_{G(ON)} = 2.7\Omega$ $R_{G(OFF)} = 2.7\Omega$ $L_S \sim 100\text{nH}$		1250		ns	
t_f	Fall time			170		ns	
E_{OFF}	Turn-off energy loss				130		mJ
$t_{d(on)}$	Turn-on delay time				250		ns
t_r	Rise time				250		ns
E_{ON}	Turn-on energy loss				80		mJ
Q_{rr}	Diode reverse recovery charge	Diode arm		80		μC	
I_{rr}	Diode reverse recovery current	$I_F = 800\text{A}$ $V_{CE} = 600\text{V}$		380		A	
E_{rec}	Diode reverse recovery energy	$dI_F/dt = 4200\text{A}/\mu\text{s}$		30		mJ	

$T_{case} = 125^{\circ}\text{C}$ unless stated otherwise

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units	
$t_{d(off)}$	Turn-off delay time	$I_C = 800\text{A}$ $V_{GE} = \pm 15\text{V}$ $V_{CE} = 600\text{V}$ $R_{G(ON)} = 2.7\Omega$ $R_{G(OFF)} = 2.7\Omega$ $L_S \sim 100\text{nH}$		1500		ns	
t_f	Fall time			200		ns	
E_{OFF}	Turn-off energy loss				160		mJ
$t_{d(on)}$	Turn-on delay time				400		ns
t_r	Rise time				220		ns
E_{ON}	Turn-on energy loss				120		mJ
Q_{rr}	Diode reverse recovery charge	Diode arm		160		μC	
I_{rr}	Diode reverse recovery current	$I_F = 800\text{A}$ $V_{CE} = 600\text{V}$		450		A	
E_{rec}	Diode reverse recovery energy	$dI_F/dt = 4000\text{A}/\mu\text{s}$		60		mJ	

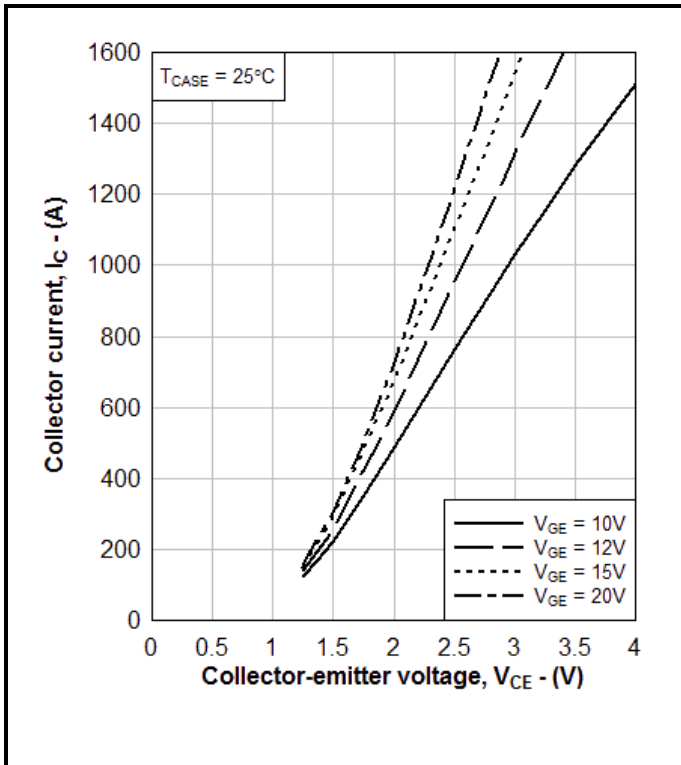


Fig. 3 Typical output characteristics

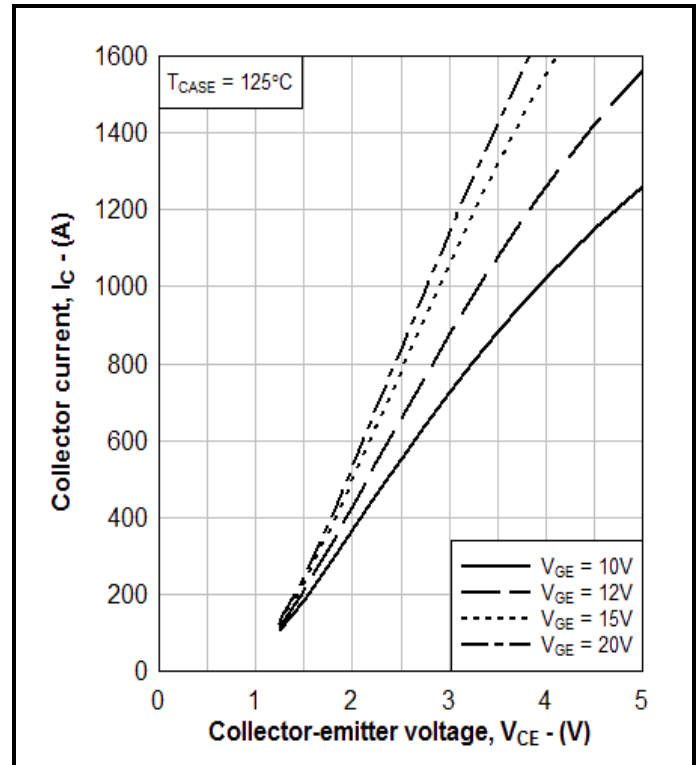


Fig. 4 Typical output characteristics

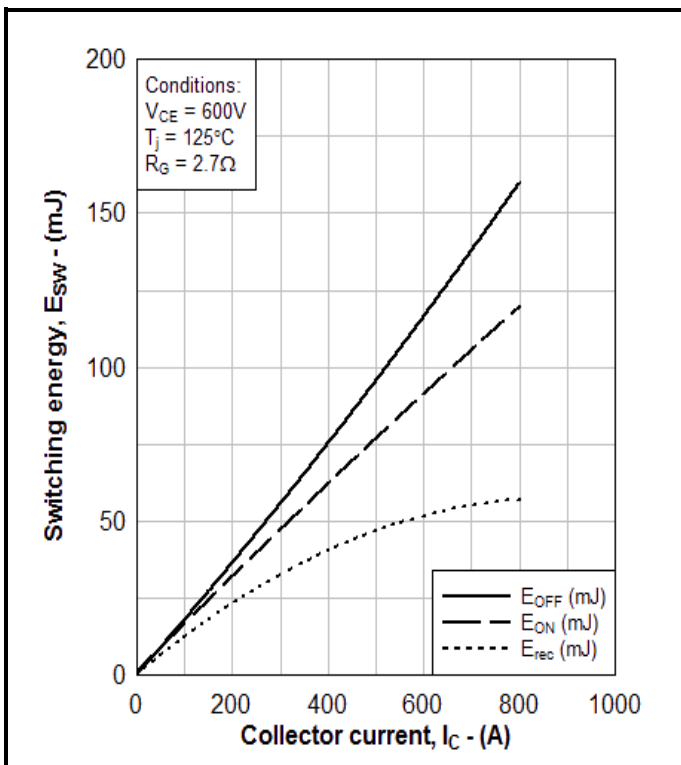


Fig. 5 Typical switching energy vs collector current

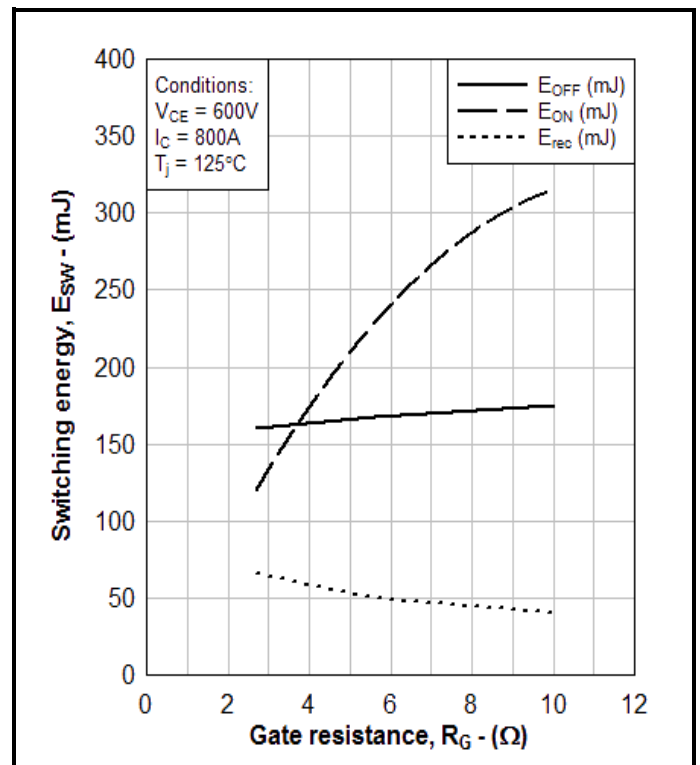


Fig. 6 Typical switching energy vs gate resistance

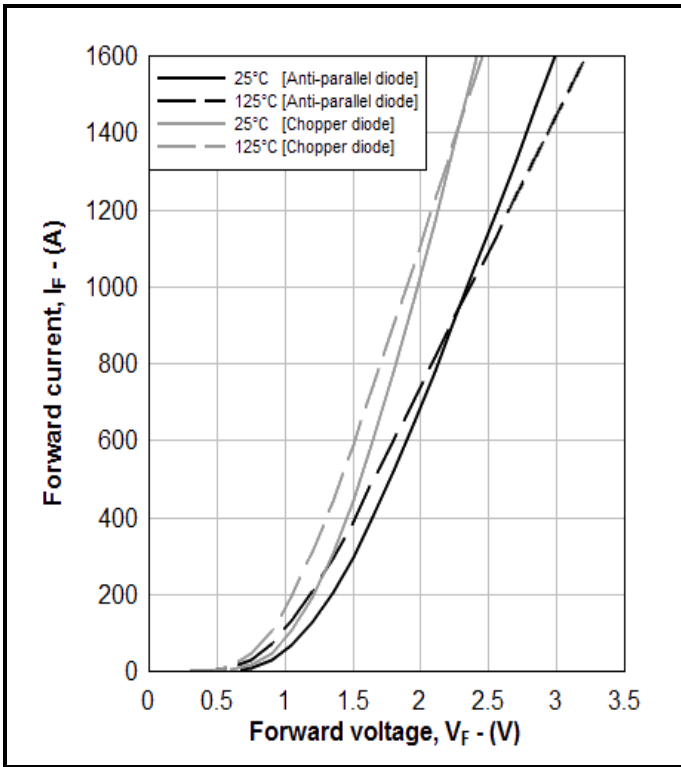


Fig. 7 Diode typical forward characteristics

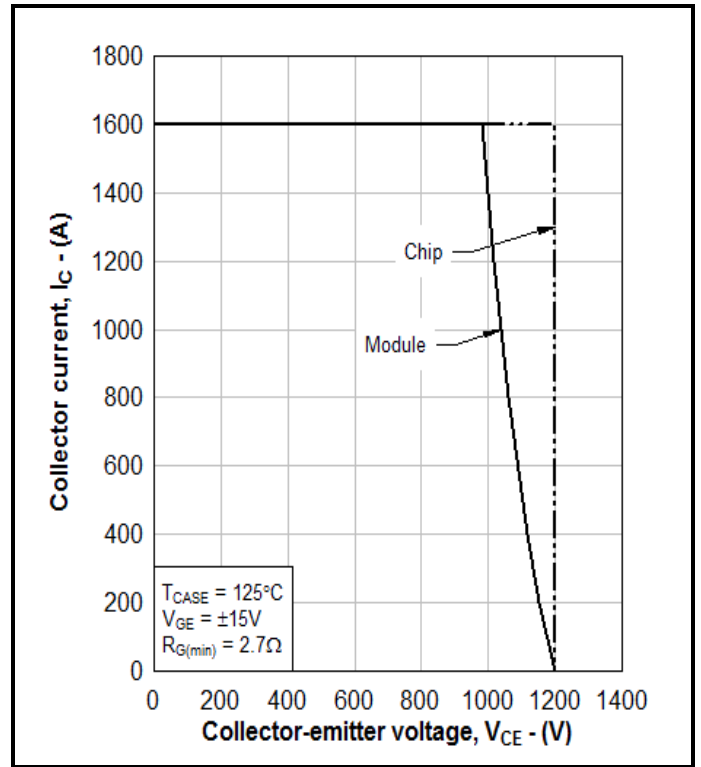


Fig. 8 Reverse bias safe operating area

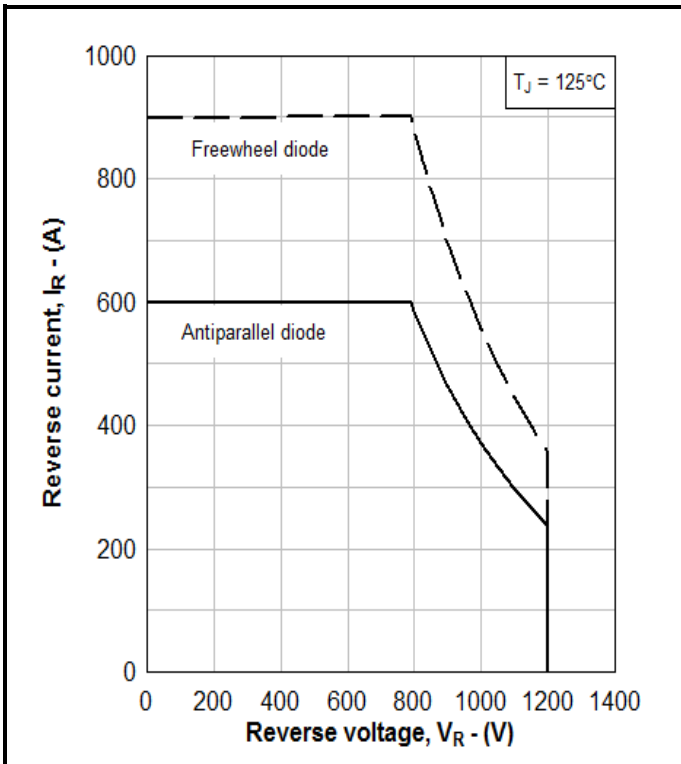


Fig. 9 Diode reverse bias safe operating area

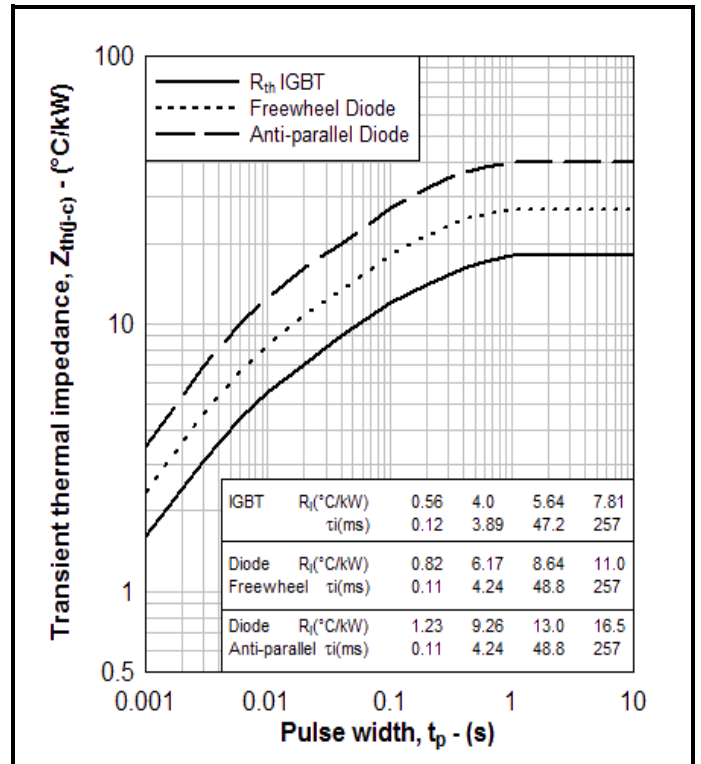


Fig. 10 Transient thermal impedance

PACKAGE DETAILS

For further package information, please visit our website or contact Customer Services.
 All dimensions in mm, unless stated otherwise.
DO NOT SCALE.

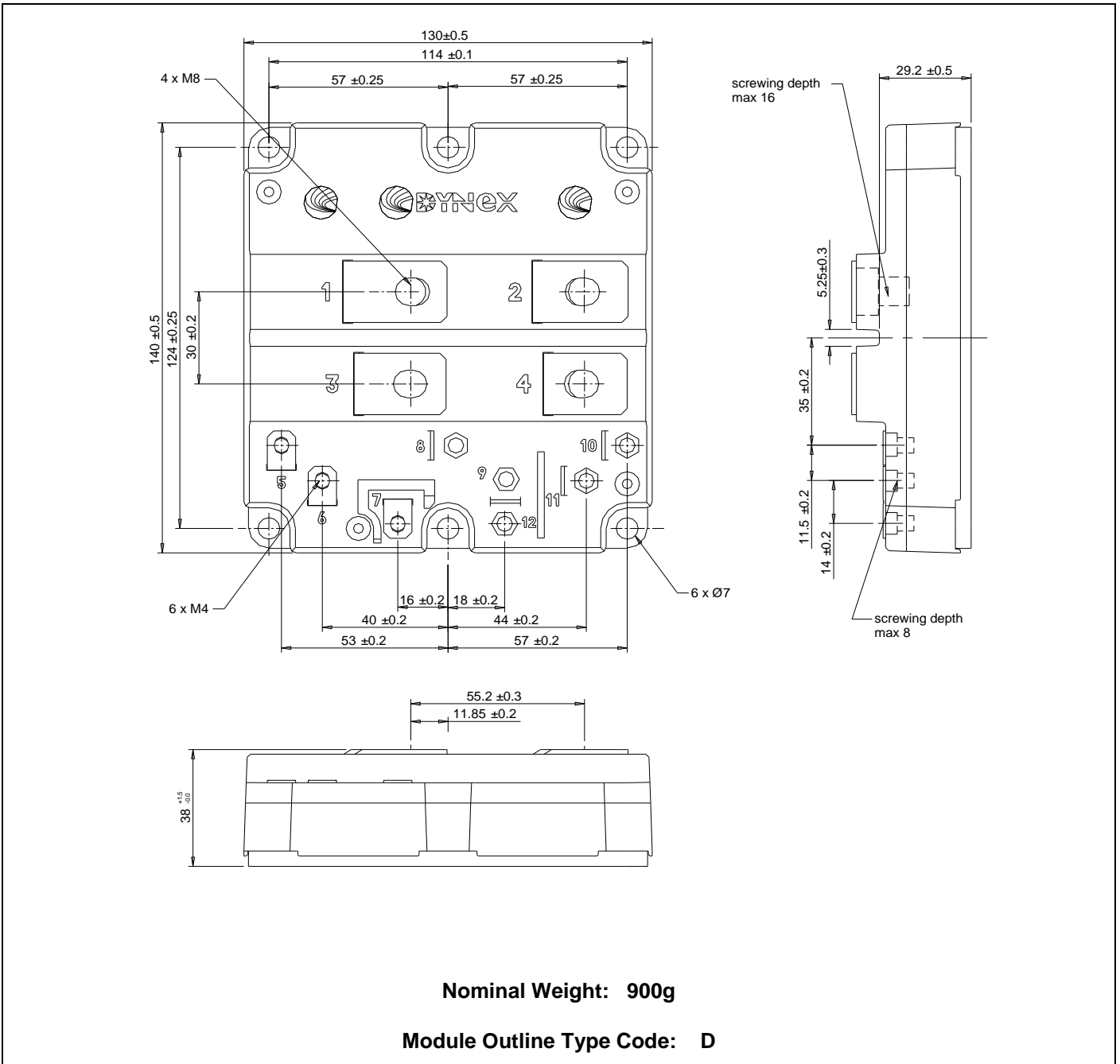


Fig. 11 Module outline drawing

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